

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-8. (withdrawn)

9. (currently amended) A film formation method comprising the steps of:
setting different temperatures to a material plural times ~~in an evaporation source~~
~~comprising the material to purify the~~ form a purified material by sublimation ~~stepwise~~; and
forming a thin film on a substrate using the purified material immediately after the setting
step.

10. (currently amended) A The film formation method according to claim 9, wherein the material is an EL material.

11-21. (withdrawn)

22. (original) A film formation method comprising the steps of:
evaporating a material in a first system controlled to a first temperature;
controlling a second system to a second temperature to change the material into a first gas
and a first solid;
removing the first gas;
evaporating the first solid in the second system controlled to the first temperature;
controlling a third system to a third temperature to change the evaporated first solid into a
second gas and a second solid; and
forming a thin film using the second gas over a substrate.

23. (currently amended) A film formation method comprising the steps of:
evaporating a material in a first system controlled to a first temperature;
controlling a second system to a second temperature to change the material into a gas and
a solid;
removing the gas; and
evaporating the solid to form an evaporation in the second system controlled to the first
temperature; and
forming a thin film on a substrate using the evaporation immediately after the second
evaporating step.

24. (currently amended) A film formation method comprising the steps of:
evaporating a material in a first system controlled to a first temperature;
controlling a second system to a second temperature to change the material into a gas and
a solid; and
forming a thin film using the gas over a substrate immediately after the controlling step.

25. (currently amended) A The film formation method according to claim 22, wherein the
material is an EL material.

26. (currently amended) A The film formation method according to claim 23, wherein the
material is an EL material.

27. (currently amended) A The film formation method according to claim 24, wherein the
material is an EL material.

28. (previously presented) A film formation method comprising the steps of:
evaporating a solid including an EL material to form a gas including the EL material;

moving the gas including the EL material with a carrier gas, and a temperature of the gas including the EL material gradually decrease in accordance with the moving;
precipitating the EL material in one position to form a precipitated EL material; and
forming a thin film using the precipitated EL material.

29. (currently amended) A The film formation method according to claim 28, wherein the carrier gas is one of nitrogen and a noble gas.

30. (currently amended) A The film formation method according to claim 28, wherein the moving step is conducted in a reduced pressure state.

31. (previously presented) A film formation method comprising the steps of:
evaporating a solid including an EL material to form a gas including the EL material in a first chamber;

moving the gas including the EL material with a carrier gas in a second chamber, and a temperature of the gas including the EL material gradually decrease in accordance with the moving;

precipitating the EL material in one position to form a precipitated EL material in the second chamber; and

forming a thin film using the precipitated EL material in a third chamber.

32. (currently amended) A The film formation method according to claim 31, wherein the carrier gas is one of nitrogen and a noble gas.

33. (currently amended) A The film formation method according to claim 31, wherein the moving step is conducted in a reduced pressure state.